

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): En-Hsing Chen, et al.

Assignee: SanDisk 3D LLC

Title: NAND Memory Array Incorporating Multiple Write Pulse Programming of Individual Memory Cells and Method for Operation of Same

Patent No.: 7,023,739 B2 Issued: April 4, 2006

Atty. Docket No.: 023-0030

June 2, 2006

ATTN: Certificate of Correction Branch
COMMISSIONER FOR PATENTS
P.O. Box 1450
Alexandria, VA 22313-1450

**REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT—
APPLICANT'S MISTAKE (37 C.F.R. § 1.323)**

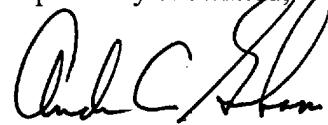
1. It is noted that one or more error(s) appears in this patent of a clerical, typographical, or minor nature or character, as more fully described below. Such error(s) occurred in good faith. Correction thereof does not involve such changes in the patent as would constitute new matter or would require re-examination. A certificate of correction is requested.
2. The exact page and line number where the error(s) occur(s) in the application is(are):
Application filed December 5, 2003, page 33, lines 19 and 20; page 40, line 13; and page 42, line 31.
3. There are also mistakes to be corrected that were made by the Office. The corrections being sought are all shown correctly in the Application filed December 5, 2003.
4. Attached hereto is Form PTO/SB/44 (PTO-1050) suitable for printing.
5. Please send the Certificate to:

Andrew C. Graham
Zagorin O'Brien Graham LLP
7600B N. Capital of Texas Hwy, Suite 350
Austin, TX 78731

6. The \$100.00 fee required under 37 C.F.R. § 1.20(a) is submitted as follows:

- This fee is being paid as directed in an electronic submission of this paper.
- A check is enclosed for this fee.
- Please charge this fee to Deposit Account 50-0631. A duplicate of this request is attached.
- The Commissioner is hereby authorized to charge any deficiency in fees and any additional fees that may be required by this paper, and to similarly credit any overpayment, to Deposit Account 50-0631.

Respectfully submitted,



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(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO : 7,023,739 B2

DATED : April 4, 2006

INVENTOR(S) : En-Hsing Chen, Andrew J. Walker, Roy E. Scheuerlein, Sucheta Nallamothu, Alper Ilkbahar, and Luca G. Fasoli

It is certified that error(s) appear(s) in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 22:

Line 43, the words "programmed stated" should read -- programmed state -- .

Column 23:

Line 4, the word "suicide" should read -- silicide -- .

Column 27:

Line 1, the words "A 2556 kb 3.0V ITIMTJ" should read -- A 256 kb 3.0V 1M1MTJ -- .

Column 28:

Line 47, the word "use" should read -- used -- .

Column 36:

Line 18, the word "NAND)" should read -- NAND -- .

MAILING ADDRESS OF SENDER:

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PATENT NO. 7,023,739 B2